

The present application is related to the following listed two applications: Serial No. 10/034,067, filed on 12/28/2001, entitled "Buried Power Buss Utilized As A Sinkers for High Current, High Power Semiconductor Devices and A Method for Providing the Same;" and Serial No. 10/034,279, filed on 12/28/2001, entitled "Buried Power Buss Utilized As A Ground Strap for High Current, High Power Semiconductor Devices and A Method for Providing the Same"; assigned to the assignee of the present application.

IN THE CLAIMS

16. (Amended) A semiconductor device comprising:

a semiconductor substrate, the semiconductor substrate including a plurality of device structures thereon; and

an interconnect on the semiconductor substrate, wherein the interconnect is not part of the device structure, the interconnect comprising at least one slot provided in the semiconductor substrate and at least one metal within the slot.

23. (Amended) A high current, high power interconnect on a semiconductor substrate comprising:

at least one slot provided in the semiconductor substrate; and

at least one metal within the slot, wherein the interconnect is not part of any of a plurality of device structures on the substrate.

24. (Amended) The high current, high power interconnect of claim 23 wherein the semiconductor substrate comprises:

a substrate region; and